

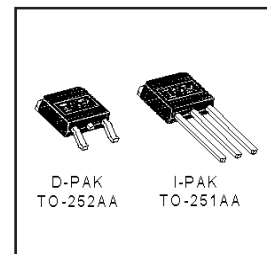
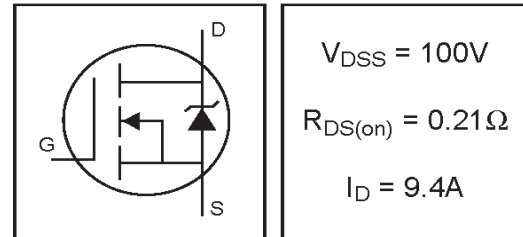
# IRFR/U120NPbF

- Surface Mount (IRFR120N)
- Straight Lead (IRFU120N)
- Advanced Process Technology
- Fast Switching
- Fully Avalanche Rated
- Lead-Free

## Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve the lowest possible on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient device for use in a wide variety of applications.

The D-PAK is designed for surface mounting using vapor phase, infrared, or wave soldering techniques. The straight lead version (IRFU series) is for through-hole mounting applications. Power dissipation levels up to 1.5 watts are possible in typical surface mount applications.



## Absolute Maximum Ratings

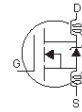
	Parameter	Max.	Units
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	9.4	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	6.6	
$I_{DM}$	Pulsed Drain Current ①⑥	38	
$P_D @ T_C = 25^\circ\text{C}$	Power Dissipation	48	W
	Linear Derating Factor	0.32	W/°C
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	V
$E_{AS}$	Single Pulse Avalanche Energy②⑥	91	mJ
$I_{AR}$	Avalanche Current①⑥	5.7	A
$E_{AR}$	Repetitive Avalanche Energy①⑥	4.8	mJ
$dv/dt$	Peak Diode Recovery $dv/dt$ ③	5.0	V/ns
$T_J$	Operating Junction and	-55 to + 175	°C
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case )	

## Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	3.1	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB mount) **	—	50	
$R_{\theta JA}$	Junction-to-Ambient	—	110	

## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	100	---	---	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	---	0.12	---	$V/^\circ C$	Reference to $25^\circ C, I_D = 1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	---	---	0.21		$V_{GS} = 10V, I_D = 5.6A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	2.0	---	4.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
$g_{fs}$	Forward Transconductance	2.7	---	---	S	$V_{DS} = 25V, I_D = 5.7A$ ⑥
$I_{DSS}$	Drain-to-Source Leakage Current	---	---	25	$\mu A$	$V_{DS} = 100V, V_{GS} = 0V$
		---	---	250		$V_{DS} = 80V, V_{GS} = 0V, T_J = 150^\circ C$
$I_{GSS}$	Gate-to-Source Forward Leakage	---	---	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	---	---	-100		$V_{GS} = -20V$
$Q_g$	Total Gate Charge	---	---	25	nC	$I_D = 5.7A$
$Q_{gs}$	Gate-to-Source Charge	---	---	4.8		$V_{DS} = 80V$
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	---	---	11		$V_{GS} = 10V$ , See Fig. 6 and 13 ④ ⑥
$t_{d(on)}$	Turn-On Delay Time	---	4.5	---	ns	$V_{DD} = 50V$
$t_r$	Rise Time	---	23	---		$I_D = 5.7A$
$t_{d(off)}$	Turn-Off Delay Time	---	32	---		$R_G = 22\Omega$
$t_f$	Fall Time	---	23	---		$R_D = 8.6\Omega$ , See Fig. 10 ④ ⑥
$L_D$	Internal Drain Inductance	---	4.5	---	nH	Between lead, 6mm (0.25in.) from package and center of die contact ⑤
$L_S$	Internal Source Inductance	---	7.5	---		
$C_{ISS}$	Input Capacitance	---	330	---	pF	$V_{GS} = 0V$
$C_{OSS}$	Output Capacitance	---	92	---		$V_{DS} = 25V$
$C_{RSS}$	Reverse Transfer Capacitance	---	54	---		$f = 1.0MHz$ , See Fig. 5 ⑥



## Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	---	---	9.4	A	MOSFET symbol showing the integral reverse p-n junction diode.
$I_{SM}$	Pulsed Source Current (Body Diode) ① ⑥	---	---	38		
$V_{SD}$	Diode Forward Voltage	---	---	1.3	V	$T_J = 25^\circ C, I_S = 5.5A, V_{GS} = 0V$ ④
$t_{rr}$	Reverse Recovery Time	---	99	150	ns	$T_J = 25^\circ C, I_F = 5.7A$
$Q_{rr}$	Reverse Recovery Charge	---	390	580	nC	$di/dt = 100A/\mu s$ ④ ⑥
$t_{on}$	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$ )				

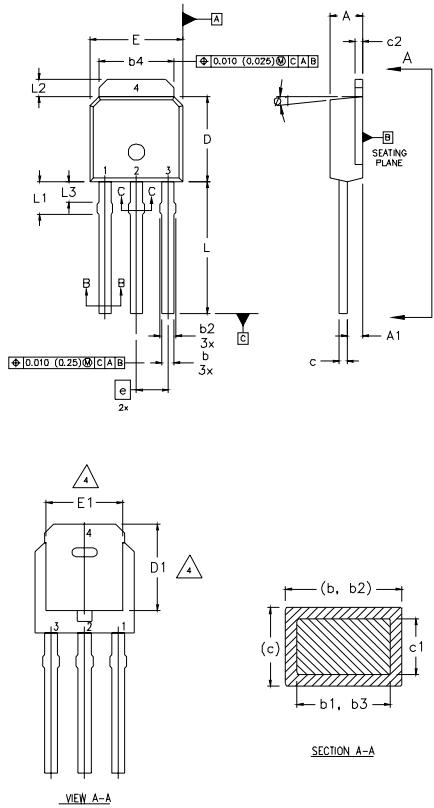
### Notes:

- ① Repetitive rating: pulse width limited by max. junction temperature. ( See fig. 11 )
- ②  $V_{DD} = 25V$ , starting  $T_J = 25^\circ C$ ,  $L = 4.7mH$ ,  $R_G = 25\Omega$ ,  $I_{AS} = 5.7A$ . (See Figure 12)
- ③  $I_{SD} \leq 5.7A$ ,  $di/dt \leq 240A/\mu s$ ,  $V_{DD} \leq V_{(BR)DSS}$ ,  $T_J \leq 175^\circ C$
- ④ Pulse width  $\leq 300\mu s$ ; duty cycle  $\leq 2\%$
- ⑤ This is applied for I-PAK,  $L_S$  of D-PAK is measured between lead and center of die contact
- ⑥ Uses IRF520N data and test conditions

\*\* When mounted on 1" square PCB (FR-4 or G-10 Material ) .  
For recommended footprint and soldering techniques refer to application note #AN-994

## I-Pak (TO-251AA) Package Outline

Dimensions are shown in millimeters (inches)



**NOTES:**

- 1 DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
- 2 DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
- 3 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- 4 THERMAL PAD CONTOUR OPTION WITHIN DIMENSION b4, L2, E1 & D1.
- 5 LEAD DIMENSION UNCONTROLLED IN L3.
- 6 DIMENSION b1, b3 APPLY TO BASE METAL ONLY.
- 7 OUTLINE CONFORMS TO JEDEC OUTLINE TO-251AA.
- 8 CONTROLLING DIMENSION : INCHES.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	0.086	.094	
A1	0.89	1.14	0.035	0.045	
b	0.64	0.89	0.025	0.035	
b1	0.64	0.79	0.025	0.031	4
b2	0.76	1.14	0.030	0.045	
b3	0.76	1.04	0.030	0.041	
b4	5.00	5.46	0.195	0.215	4
c	0.46	0.61	0.018	0.024	
c1	0.41	0.56	0.016	0.022	
c2	.046	0.86	0.018	0.035	
D	5.97	6.22	0.235	0.245	3, 4
D1	5.21	-	0.205	-	4
E	6.35	6.73	0.250	0.265	3, 4
E1	4.32	-	0.170	-	4
e	2.29		0.090 BSC		
L	8.89	9.60	0.350	0.380	
L1	1.91	2.29	0.075	0.090	
L2	0.89	1.27	0.035	0.050	4
L3	1.14	1.52	0.045	0.060	5
ø1	0"	15"	0"	15"	

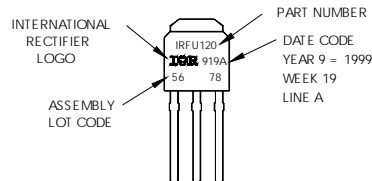
**LEAD ASSIGNMENTS**

**HEXFEEET**

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

## I-Pak (TO-251AA) Part Marking Information

EXAMPLE: THIS IS AN IRFU120 WITH ASSEMBLY LOT CODE 5678 ASSEMBLED ON WW 19, 1999 IN THE ASSEMBLY LINE "A"  
**Note:** "P" in assembly line position indicates "Lead-Free"



**OR**

